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Vishay/Siliconix
SUM23N15-73-E3

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SUM23N15-73

Vishay Siliconix

N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
150	0.073 at V_{GS} = 10 V	23
	0.077 at V_{GS} = 6 V	22.5

FEATURES

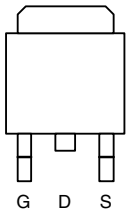
- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

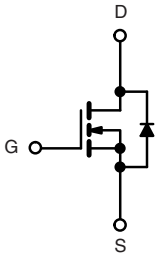
APPLICATIONS

- Primary Side Switch

TO-263



Top View



N-Channel MOSFET

Ordering Information: SUM23N15-73-E3 (Lead (Pb) free)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	23	A
	T_C = 125 °C		13.4	
Pulsed Drain Current		I_{DM}	35	
Avalanche Current		I_{AR}	25	
Repetitive Avalanche Energy[a]	L = 0.1 mH	E_{AR}	31	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	100[b]	W
	T_A = 25 °C[c]		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.5	

Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR-4 material).

SUM23N15-73

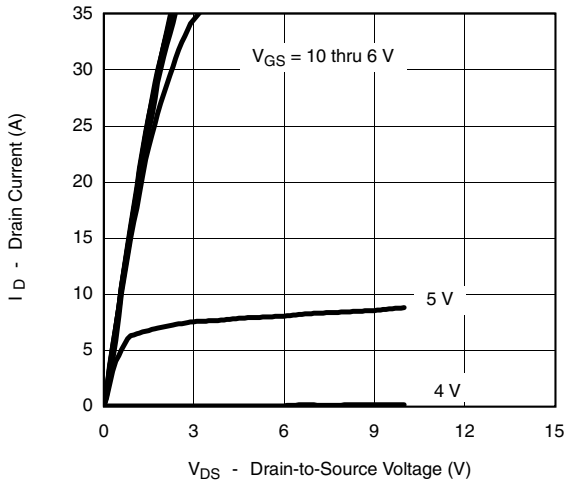
Vishay Siliconix

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	150			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 120 V, V_{GS} = 0 V			1	µA
		V_{DS} = 120 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 120 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	35			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15 A		0.059	0.073	Ω
		V_{GS} = 10 V, I_D = 15 A, T_J = 125 °C			0.140	
		V_{GS} = 10 V, I_D = 15 A, T_J = 175 °C			0.168	
		V_{GS} = 6 V, I_D = 10 A		0.062	0.077	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 25 A	10			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		1290		pF
Output Capacitance	C_{oss}			160		
Reverse Transfer Capacitance	C_{rss}			70		
Total Gate Charge[c]	Q_g	V_{DS} = 75 V, V_{GS} = 10 V, I_D = 23 A		22	35	nC
Gate-Source Charge[c]	Q_{gs}			6		
Gate-Drain Charge[c]	Q_{gd}			7.5		
Gate Resistance	R_G			4		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 75 V, R_L = 3.26 Ω I_D ≅ 23 A, V_{GEN} = 10 V, R_G = 2.5 Ω		10	15	ns
Rise Time[c]	t_r			60	90	
Turn-Off Delay Time[c]	$t_{d(off)}$			30	43	
Fall Time[c]	t_f			45	70	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)[b]						
Continuous Current	I_S				35	A
Pulsed Current	I_{SM}				23	
Forward Voltage[a]	V_{SD}	I_F = 23 A, V_{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 23 A, dI/dt = 100 A/µs		100	150	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$			5	8	A
Reverse Recovery Charge	Q_{rr}			0.25	0.6	µC

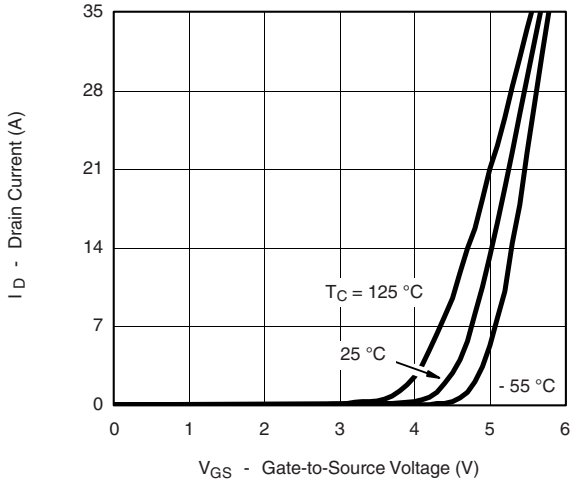
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

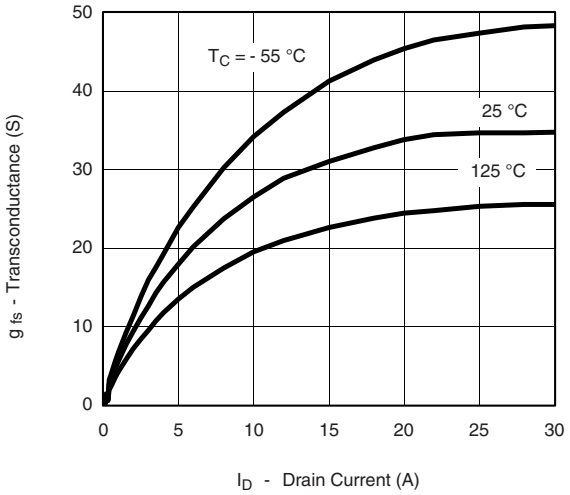
TYPICAL CHARACTERISTICS (25 °C unless noted)



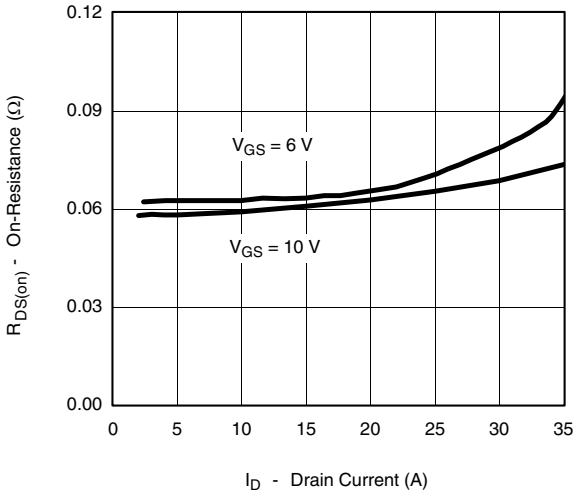
Output Characteristics



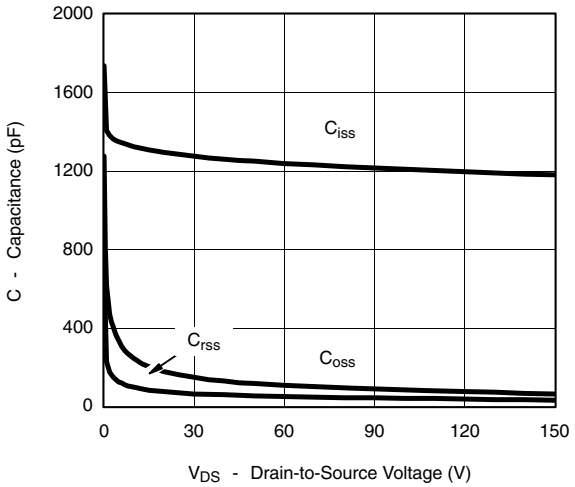
Transfer Characteristics



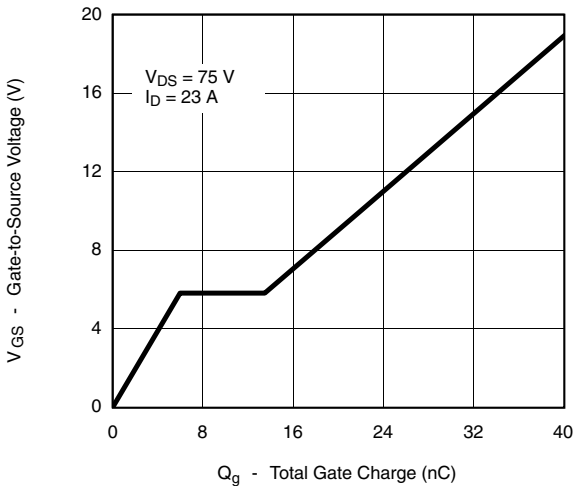
Transconductance



On-Resistance vs. Drain Current

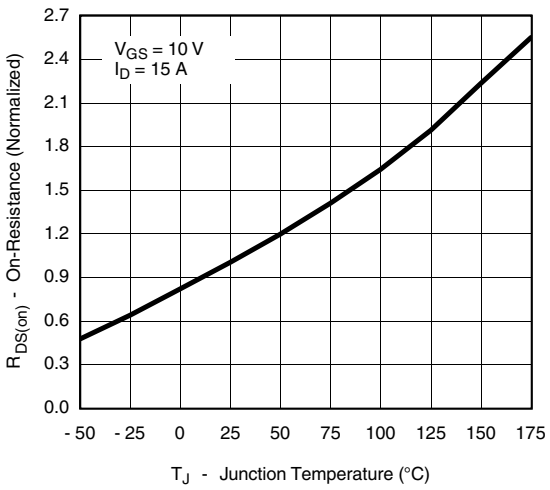


Capacitance

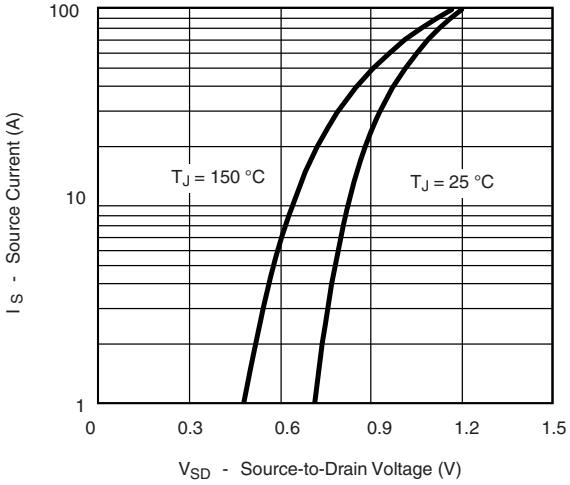


Gate Charge

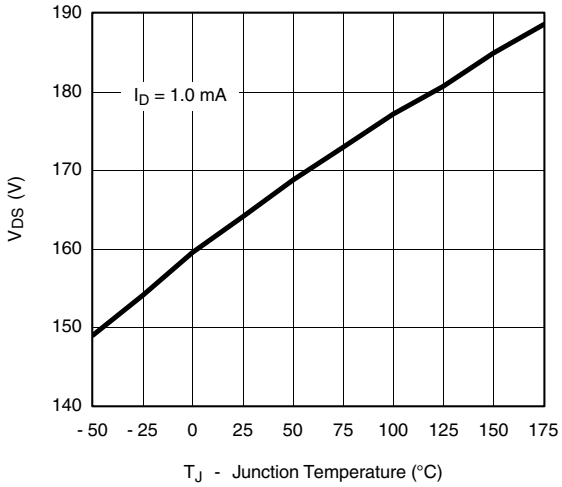
TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

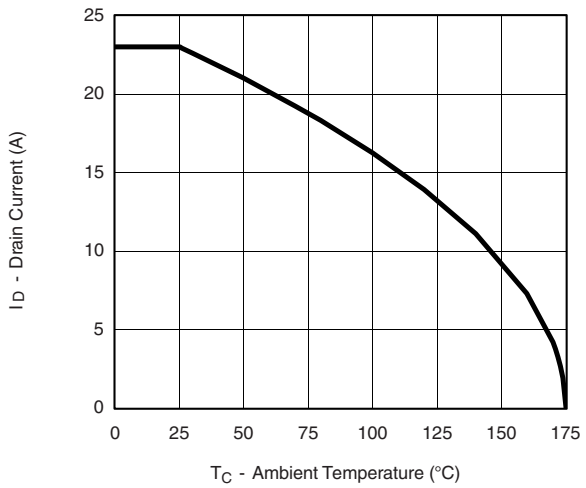


Source-Drain Diode Forward Voltage

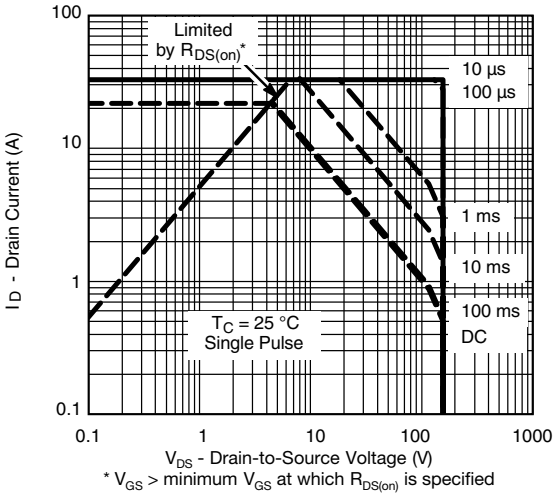


Drain Source Breakdown vs. Junction Temperature

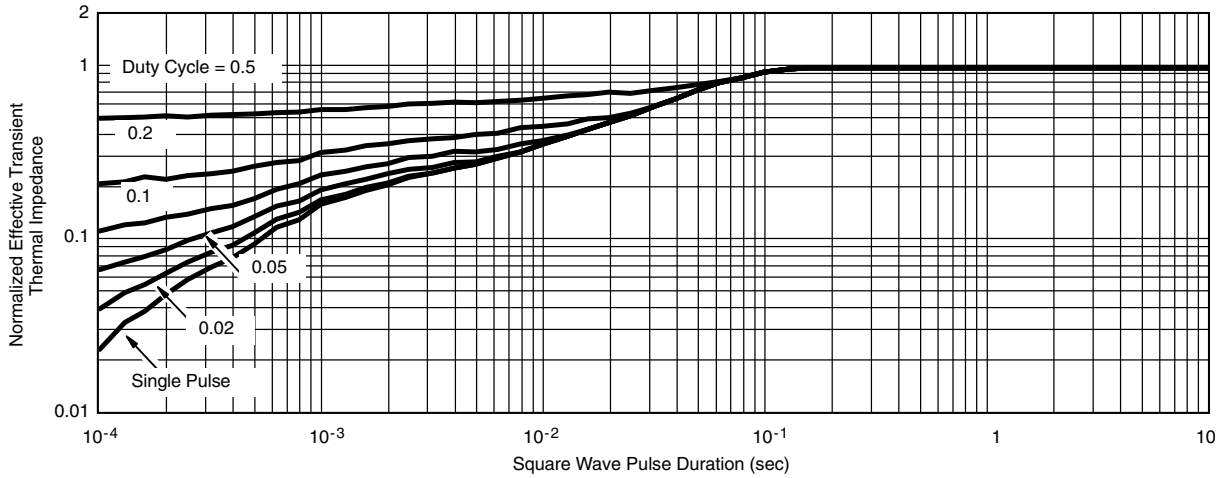
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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